



HIGH VOLTAGE SILICON RECTIFIERS

- SMALL SIZE MOLDED PACKAGE
- PRV 15,000 TO 40,000 VOLTS
- FAST RECOVERY
- AVALANCHE CHARACTERISTICS
- LOW LEAKAGE



EDI Type	PRV (Volts)	REVERSE RECOVERY TIME IN NANoseconds @25 °C (Fig.4)	MAXIMUM FORWARD VOLTAGE DROP @25mA
CRVT 150	15,000	100	35 Volts
CRVT 200	20,000	100	35 Volts
CRVT 250	25,000	100	35 Volts
CRVT 300	30,000	100	48 Volts
CRVT 400	40,000	100	60 Volts

ELECTRICAL CHARACTERISTICS (at T_A=25 °C Unless Otherwise Specified)

Average Rectified Forward Current @ 75°C, (Fig. 1)	25 mA
Max Peak Surge Current (8.3ms) (Fig.2)	3 Amp
Max DC Reverse Current @ PRV and 25°C	1 μA
Max DC Reverse Current @ PRV and 100 °C	25 μA
Ambient Operating Temperature Range	-55 °C to +125 °C
Storage Temperature Range	-55°C to +150 °C

NOTES:

- 1.It is recommended that a proper heat sink be used on the terminals of this device between the body and soldering point to prevent damage from excess heat.
- 2.If operated over 10,000v/inch in length, devices should be immersed in oil or re - encapsulated.

EDI reserves the right to change these specifications at any time without notice.

FIG.1

OUTPUT CURRENT vs AMBIENT TEMPERATURE

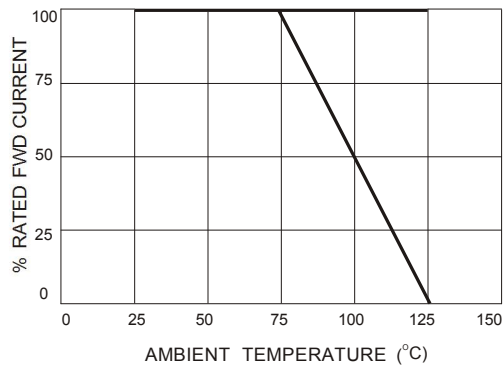


FIG.2

NON-REPETITIVE SURGE CURRENT

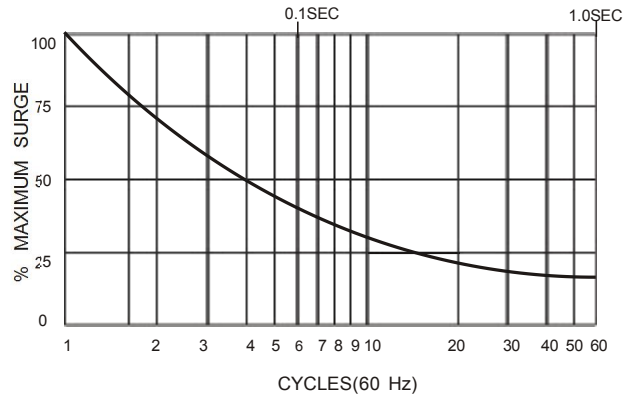


FIG.3

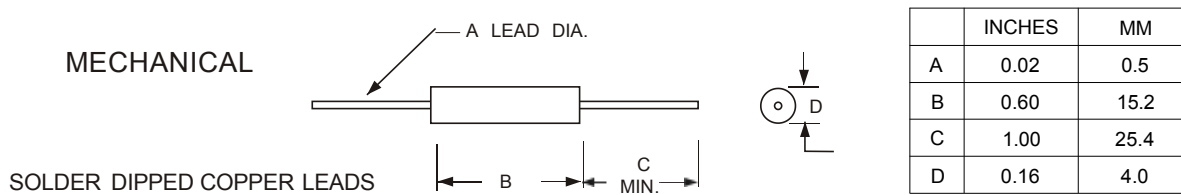
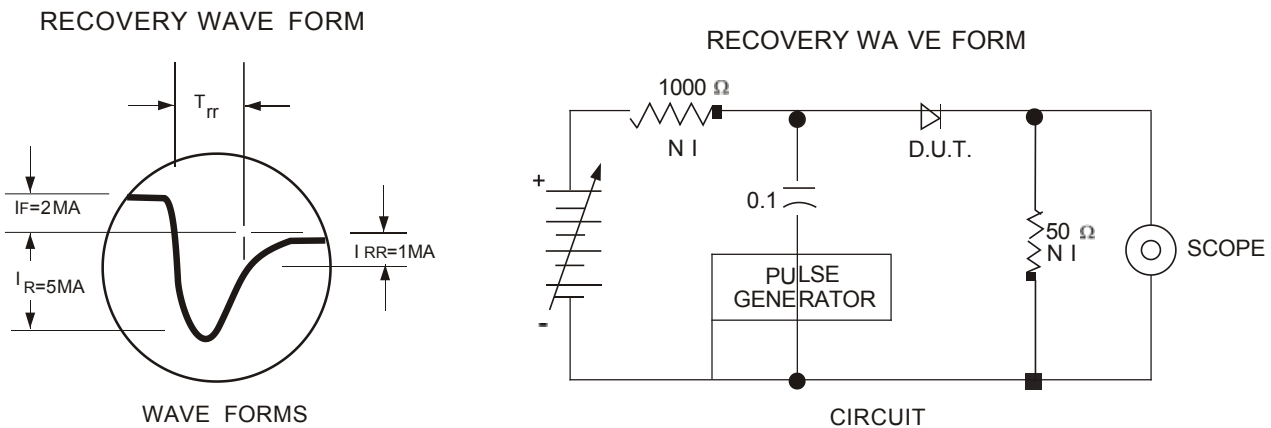


FIG.4

REVERSE RECOVERY TEST METHOD



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